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AMENDMENT TRANSMITTAL LETTER							Docket No. 1592-0155PUS1	
Application No.		Filing I		Examiner			Art Unit	
10/534,695-Conf. #8694		May 13, 2005		<u>N</u>	M. D. Harrison		2813	
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Marc S. Weiner Attorney Reg. N				•				
BIRCH, STEWA 8110 Gatehous Suite 100 East P.O. Box 747 Falls Church, V (703) 205-8000	e Road /irginia 22040-		LP					



Docket No.: 1592-0155PUS1

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Masashi NAKAMURA et al.

Application No.: 10/534,695

Confirmation No.: 8694

Filed: May 13, 2005

Art Unit: 2813

For: EPITAXIAL GROWTH METHOD AND

SUBSTRATE FOR EPITAXIAL GROWTH

Examiner: M. D. Harrison

RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated August 8, 2006, please amend the above-identified U.S. patent application as follows:

Remarks/Arguments begin on page 2 of this paper.